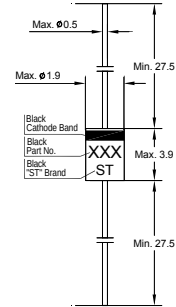


1N914, 1N914A, 1N914B

Silicon Epitaxial Planar Switching Diode

Features

- Fast switching speed
- High reliability



Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	75 200	mA
Forward Continuous Current	I_{FM}	150 300	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	1 1 4	A
Power Dissipation	P_{tot}	500	mW
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 175	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage	V_F	0.62	0.72	V
at $I_F = 5\text{ mA}$				
at $I_F = 100\text{ mA}$		-	1	
at $I_F = 10\text{ mA}$		-	1	
at $I_F = 20\text{ mA}$		-	1	
Reverse Current	I_R	-	25	nA
at $V_R = 20\text{ V}$		-	5	μA
at $V_R = 75\text{ V}$		-	50	μA
at $V_R = 20\text{ V}, T_j = 150^\circ\text{C}$				
Diode Capacitance	C_j	-	4	pF
at $V_R = 0, f = 1\text{ MHz}$				
Reverse Recovery Time	t_{rr}	-	4	ns
at $I_F = 10\text{ mA}$ to $I_R = 1\text{ mA}, V_R = 6\text{ V}, R_L = 100\ \Omega$				

